

## **ABSTRACT**

### **EPITAXIAL REACTION DEVICE**

Disclosed is an epitaxial reaction device. The epitaxial reaction device includes: a conveying apparatus and at least one reaction apparatus. The reaction apparatus includes a high-temperature reaction chamber, a gas supply module, and a gas extraction module. The high-temperature reaction chamber is used for providing an environmental condition required during processing of a wafer. The gas supply module and the gas extraction module are oppositely provided in the high-temperature reaction chamber. The gas supply module is used for supplying reaction gas to the high-temperature reaction chamber, and the gas extraction module is used for extracting gas remained after reaction. The conveying apparatus is provided on the high-temperature reaction chamber and located on a same side as the gas supply module. The conveying apparatus is used for taking out and placing the wafer.

Figure 1